

Giriraj Jnawali

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7638375/publications.pdf>

Version: 2024-02-01

34
papers

913
citations

566801

15
h-index

454577

30
g-index

35
all docs

35
docs citations

35
times ranked

1717
citing authors

#	ARTICLE	IF	CITATIONS
1	Observation of a Transient Decrease in Terahertz Conductivity of Single-Layer Graphene Induced by Ultrafast Optical Excitation. Nano Letters, 2013, 13, 524-530.	4.5	241
2	Interplay of Wrinkles, Strain, and Lattice Parameter in Graphene on Iridium. Nano Letters, 2012, 12, 678-682.	4.5	131
3	Growth temperature dependent graphene alignment on Ir(111). Applied Physics Letters, 2011, 98, .	1.5	95
4	Observation of Ground- and Excited-State Charge Transfer at the C ₆₀ /Graphene Interface. ACS Nano, 2015, 9, 7175-7185.	7.3	69
5	Lattice accommodation of epitaxial Bi(111) films on Si(001) studied with SPA-LEED and AFM. Physical Review B, 2006, 74, .	1.1	42
6	Ultrafast photoinduced band splitting and carrier dynamics in chiral tellurium nanosheets. Nature Communications, 2020, 11, 3991.	5.8	39
7	Interplay between Forward and Backward Scattering of Spin-Orbit Split Surface States of Bi(111). Nano Letters, 2013, 13, 2717-2722.	4.5	25
8	Anisotropic scattering of surface state electrons at a point defect on Bi(111). Applied Physics Letters, 2011, 98, .	1.5	24
9	Manipulation of Electronic Transport in the Bi(111) Surface State. Physical Review Letters, 2012, 108, 266804.	2.9	22
10	Revealing Optical Transitions and Carrier Recombination Dynamics within the Bulk Band Structure of Bi ₂ Se ₃ . Nano Letters, 2018, 18, 5875-5884.	4.5	21
11	Homoepitaxial growth of Bi(111). Physical Review B, 2008, 78, .	1.1	19
12	Temperature-Controlled Rotational Epitaxy of Graphene. Nano Letters, 2019, 19, 4594-4600.	4.5	19
13	Lattice-matching periodic array of misfit dislocations: Heteroepitaxy of Bi(111) on Si(001). Physical Review B, 2007, 76, .	1.1	18
14	Epitaxial Bi(111) films on Si(001): Strain state, surface morphology, and defect structure. Thin Solid Films, 2008, 516, 8227-8231.	0.8	18
15	Electric field effects in graphene/LaAlO ₃ /SrTiO ₃ heterostructures and nanostructures. APL Materials, 2015, 3, 062502.	2.2	17
16	Strong Hot Carrier Effects in Single Nanowire Heterostructures. Nano Letters, 2019, 19, 5062-5069.	4.5	13
17	Room-Temperature Quantum Transport Signatures in Graphene/LaAlO ₃ /SrTiO ₃ Heterostructures. Advanced Materials, 2017, 29, 1603488.	11.1	12
18	Two-Dimensional Electron Transport and Scattering in Bi(111) Surface States. E-Journal of Surface Science and Nanotechnology, 2010, 8, 27-31.	0.1	11

#	ARTICLE	IF	CITATIONS
19	A Raman probe of phonons and electron-phonon interactions in the Weyl semimetal NbIrTe ₄ . Scientific Reports, 2021, 11, 8155.	1.6	10
20	Lost in reciprocal space? Determination of the scattering condition in spot profile analysis low-energy electron diffraction. Review of Scientific Instruments, 2011, 82, 035111.	0.6	9
21	Barrier-free subsurface incorporation of In_3Sb_5 atoms into Bi(111) films. Physical Review B, 2015, 91, .		
22	Nanoscale dislocation patterning in Bi(111)/Si(001) heteroepitaxy. Surface Science, 2009, 603, 2057-2061.	0.8	8
23	Nucleation and initial growth in the semimetallic homoepitaxial system of Bi on Bi(111). Physical Review B, 2009, 79, .	1.1	7
24	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. Nano Research, 2020, 13, 1586-1591.	5.8	7
25	Photoconductive response of a single Au nanorod coupled to LaAlO ₃ /SrTiO ₃ nanowires. Applied Physics Letters, 2015, 106, .	1.5	6
26	Graphene-Complex-Oxide Nanoscale Device Concepts. ACS Nano, 2018, 12, 6128-6136.	7.3	6
27	Stable tungsten disilicide contacts for surface and thin film resistivity measurements. Journal of Vacuum Science & Technology B, 2009, 27, 180.	1.3	4
28	Hot carrier transport limits the displacive excitation of coherent phonons in bismuth. Applied Physics Letters, 2021, 119, .	1.5	3
29	Nanopattern Formation by Periodic Array of Interfacial Misfit Dislocations in Bi(111)/Si(001) Heteroepitaxy. Materials Research Society Symposia Proceedings, 2007, 1059, 1.	0.1	2
30	In-situ high-resolution low energy electron diffraction study of strain relaxation in heteroepitaxy of Bi(111) on Si(001): Interplay of strain state, misfit dislocation array and lattice parameter. Thin Solid Films, 2014, 570, 159-163.	0.8	2
31	Rapid onset of strain relief by massive generation of misfit dislocations in Bi(111)/Si(001) heteroepitaxy. Applied Physics Letters, 2019, 114, 081601.	1.5	2
32	Epitaxial Growth of Bi(111) on Si(001). E-Journal of Surface Science and Nanotechnology, 2009, 7, 441-447.	0.1	1
33	Band structure and polarization effects in photothermoelectric spectroscopy of a Bi ₂ Se ₃ device. Applied Physics Letters, 2022, 120, .	1.5	1
34	Wavelength scaling of strong field effects in GaAs. , 2017, , .		0